

PolarHT™ Power MOSFET

IXTK 180N15P

$$V_{DSS} = 150 \text{ V}$$

$$I_{D25} = 180 \text{ A}$$

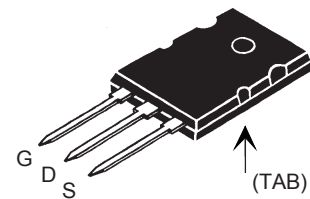
$$R_{DS(on)} \leq 10 \text{ m}\Omega$$

N-Channel Enhancement Mode
Avalanche Rated



Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	100	V	
V_{DGR}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	100	V	
V_{DSS}	Continuous	± 20	V	
V_{GSM}	Transient	± 30	V	
I_{D25}	$T_C = 25^\circ\text{C}$	180	A	
$I_{D(RMS)}$	External lead current limit	75	A	
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	380	A	
I_{AR}	$T_C = 25^\circ\text{C}$	60	A	
E_{AR}	$T_C = 25^\circ\text{C}$	100	mJ	
E_{AS}	$T_C = 25^\circ\text{C}$	4	J	
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 4 \Omega$	10	V/ns	
P_D	$T_C = 25^\circ\text{C}$	800	W	
T_J		-55 ... +175	$^\circ\text{C}$	
T_{JM}		175	$^\circ\text{C}$	
T_{stg}		-55 ... +150	$^\circ\text{C}$	
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$	
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$	
M_d	Mounting torque	1.13/10	Nm/lb.in.	
Weight		10	g	
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	150		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 500 \mu\text{A}$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$			25 μA
				250 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			10 $\text{m}\Omega$

TO-264 (IXTK)



G = Gate D = Drain
S = Source TAB = Drain

Features

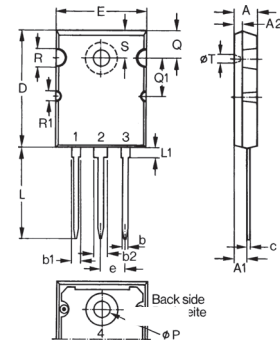
- † International standard package
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
 - easy to drive and to protect

Advantages

- † Easy to mount
- † Space savings
- † High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{ V}$; $I_D = 0.5 I_{D25}$, pulse test	55	86	S
C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		7000	pF
C_{oss}			2250	pF
C_{rss}			515	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 60\text{ A}$ $R_G = 3.3\ \Omega$ (External)		30	ns
t_r			32	ns
$t_{d(off)}$			150	ns
t_f			36	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 0.5 I_{D25}$		240	nC
Q_{gs}			55	nC
Q_{gd}			140	nC
R_{thJC}				0.18°C/W
R_{thCS}		0.15		$^\circ\text{C/W}$

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			180 A
I_{SM}	Repetitive			380 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25\text{ A}$, $-di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$, $V_{GS} = 0\text{ V}$		150	ns
Q_{RM}			2.3	μC

TO-264 (IXTK) Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
one or more of the following U.S. patents:	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

Fig. 1. Output Characteristics @ 25°C

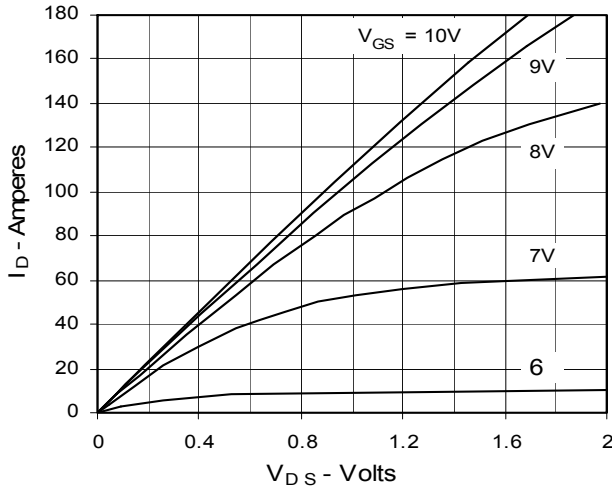


Fig. 2. Extended Output Characteristics @ 25°C

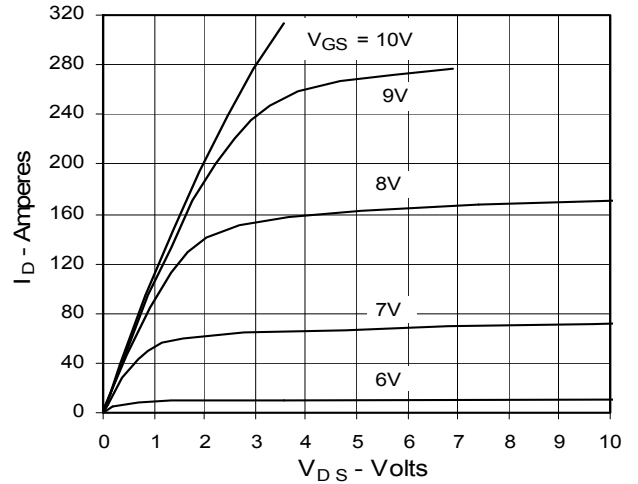


Fig. 3. Output Characteristics @ 150°C

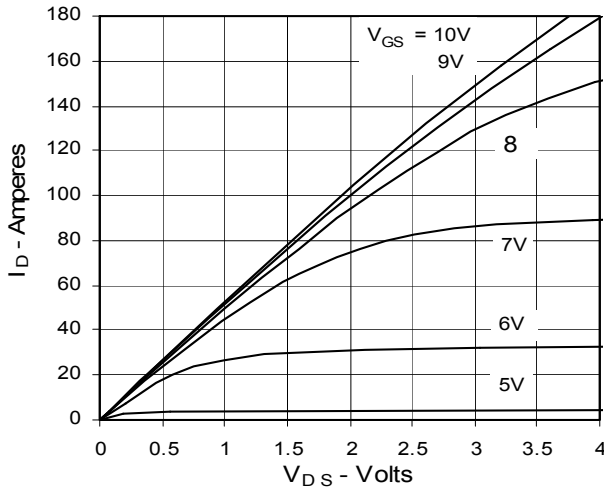


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

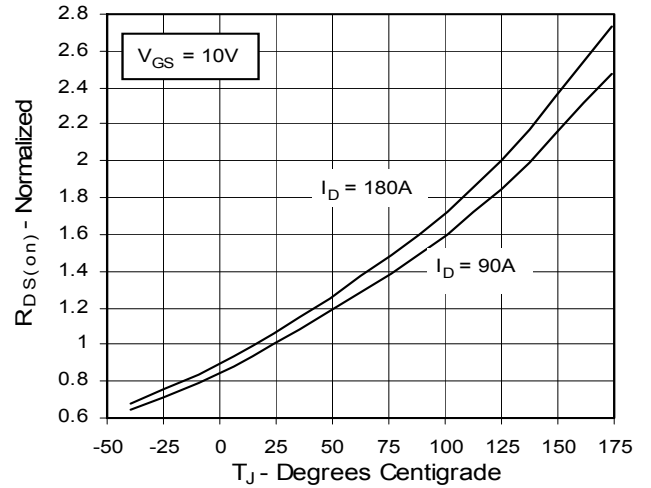


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Drain Current

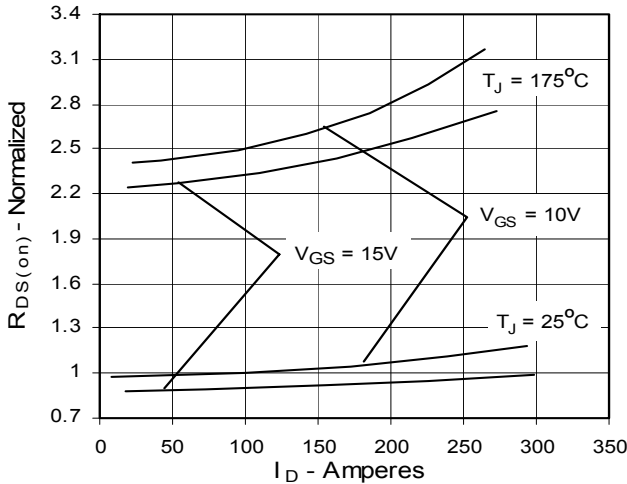


Fig. 6. Drain Current vs. Case Temperature

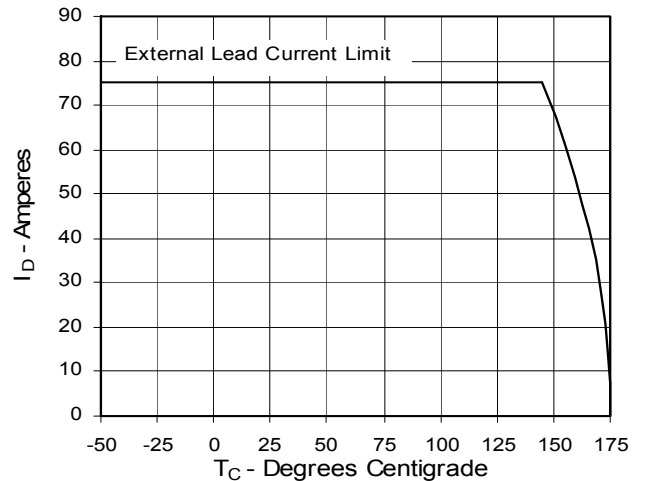


Fig. 7. Input Admittance

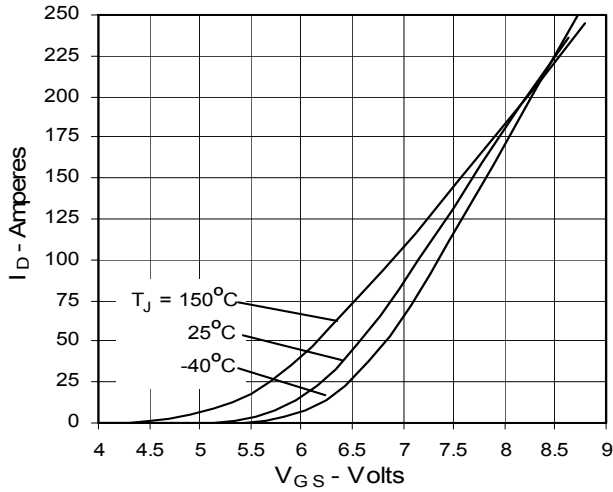


Fig. 8. Transconductance

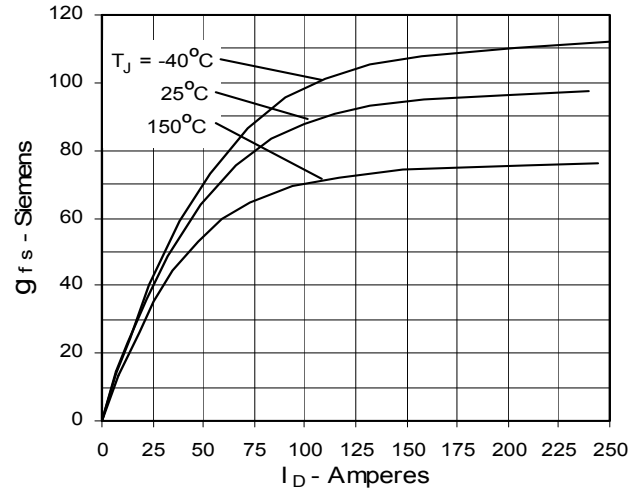


Fig. 9. Source Current vs. Source-To-Drain Voltage

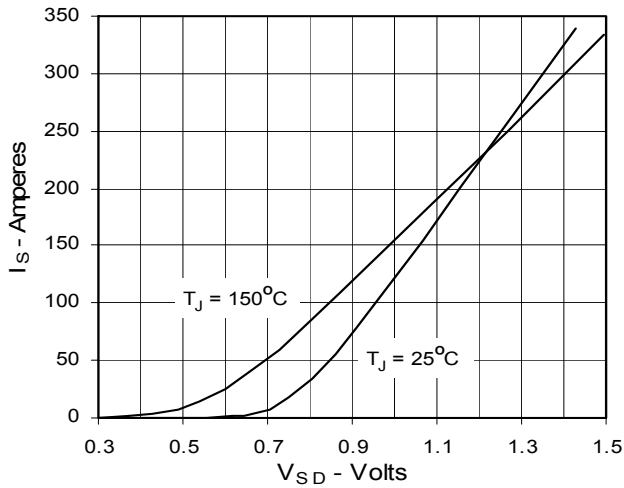


Fig. 10. Gate Charge

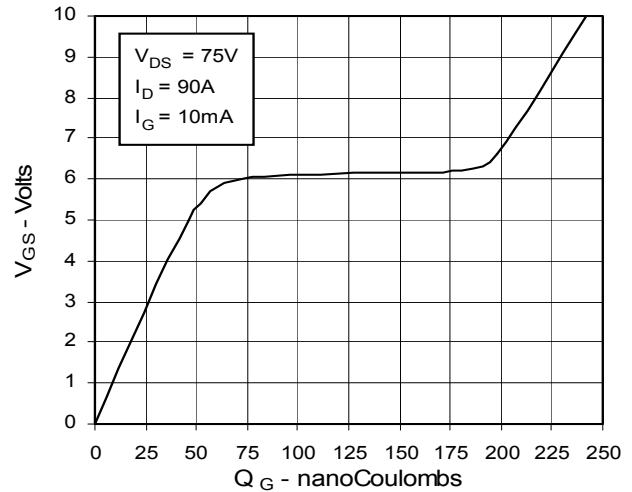


Fig. 11. Capacitance

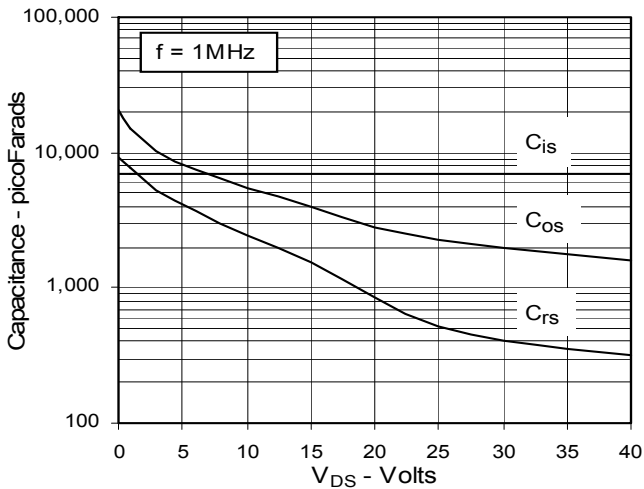


Fig. 12. Forward-Bias Safe Operating Area

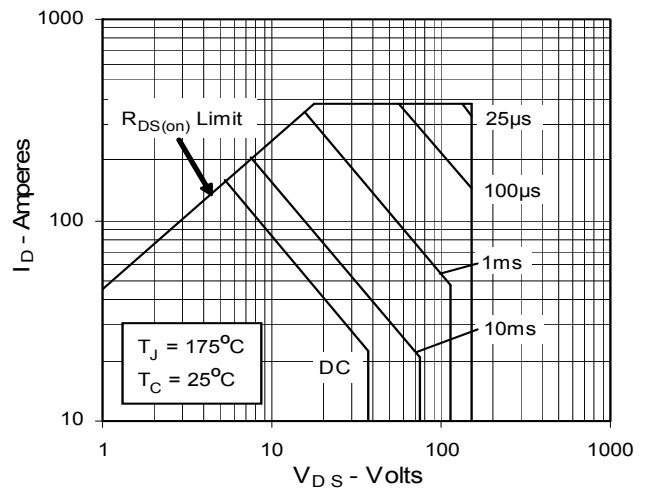


Fig. 13. Maximum Transient Thermal Resistance

